Power MOSFET 100V, 10.8mΩ, 70A, N-Channel

This N-Channel Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

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VDSS	R _{DS} (on) Max	ID Max
100V	10.8 mΩ@15V	704
	12.8 mΩ@10V	70A

Features

- Low On-Resistance
- Low Gate Charge
- High Speed Switching
- 100% Avalanche Tested
- Pb-Free and RoHS compliance

Applications

- Battery Protection
- Motor Drive
- Primary Side Switch
- Secondary Side Synchronous Rectification

SPECIFICATION

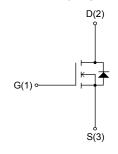
ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	100	٧
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	70	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	280	А
Power Dissipation	PD	2.1	
Tc=25°C	טי	72	W
Junction Temperature	Tj	175	°C
Storage Temperature	Tstg	–55 to +175	°C
Source Current (Body Diode)	Is	70	Α
Avalanche Energy (Single Pulse) (Note 2)	EAS	82	mJ
Lead Temperature for Soldering Purposes, 3mm from Case for 10 Seconds	TL	260	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

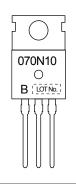
$2:V_{\mbox{\scriptsize DD}}\!\!=\!\!48V\!,\,L\!\!=\!\!100\mu\mbox{\scriptsize H},\,\mbox{\scriptsize I_{\mbox{\scriptsize AV}}}\!\!=\!\!30\mbox{\scriptsize A}\,(\mbox{\scriptsize Fig.1})$

ELECTRICAL CONNECTION N-Channel



MARKING





ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Case Steady State	R_{θ} JC	2.08	°C/W
Junction to Ambient (Note 3)	R_{θ} JA	71.4	-0/00

Note 3 : Insertion mounted

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 4)

Donomotor	Currente ed	Conditions		Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	2		4	V
Forward Transconductance	gFS	V _{DS} =10V, I _D =35A		50		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =35A, V _G S=15V		9.0	10.8	mΩ
	R _{DS} (on)2	I _D =35A, V _G S=10V		9.8	12.8	mΩ
Input Capacitance	Ciss			2,010		pF
Output Capacitance	Coss	V _{DS} =50V, f=1MHz		840		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t _d (on)			30		ns
Rise Time	t _r	Con Fig. 2		180		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		55		ns
Fall Time	tf			40		ns
Total Gate Charge	Qg			26		nC
Gate to Source Charge	Qgs	V _{DS} =48V, V _{GS} =10V, I _D =70A		9		nC
Gate to Drain "Miller" Charge	Qgd			8		nC
Forward Diode Voltage	V _{SD}	I _S =70A, V _{GS} =0V		1.1	1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		95		ns
Reverse Recovery Charge	Q _{rr}	I _S =70A, V _{GS} =0V, di/dt=100A/μs		240		nC

Note 4 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig.1 Unclamped Inductive Switching Test Circuit

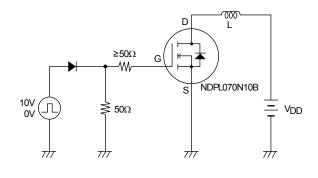


Fig.3 Reverse Recovery Time Test Circuit

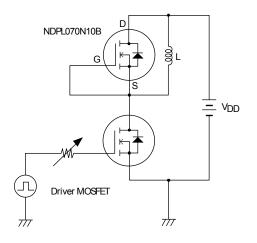
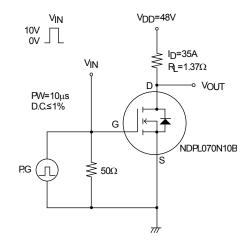
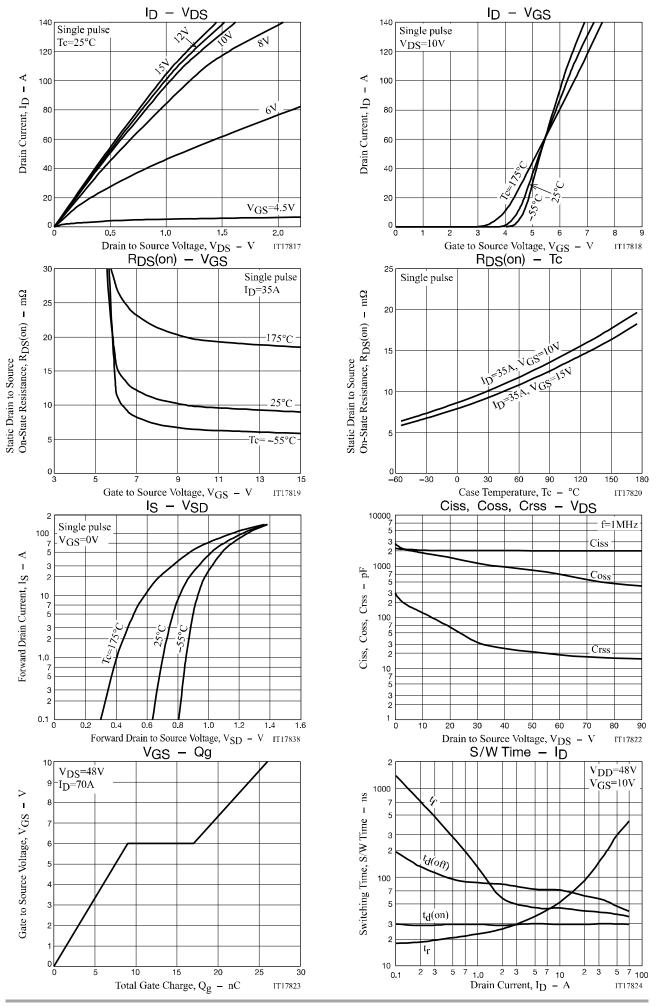
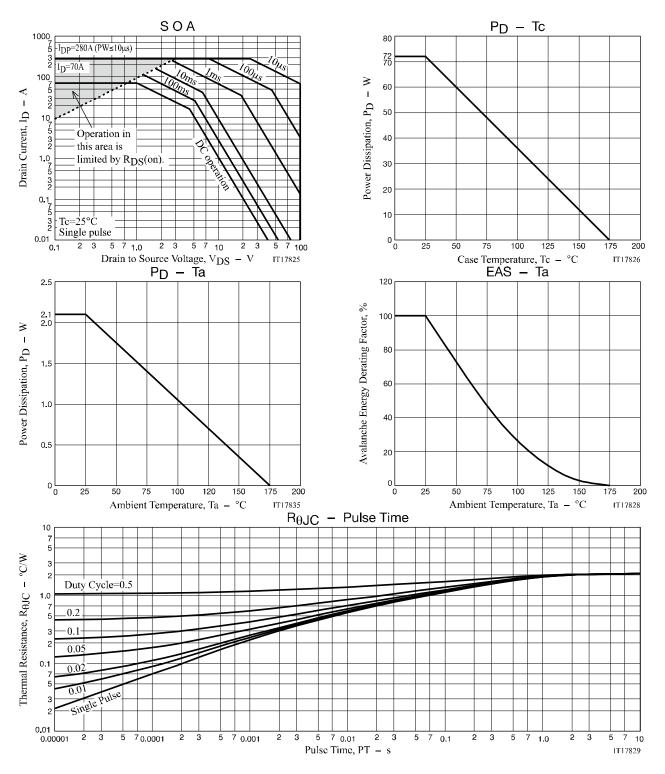


Fig.2 Switching Time Test Circuit





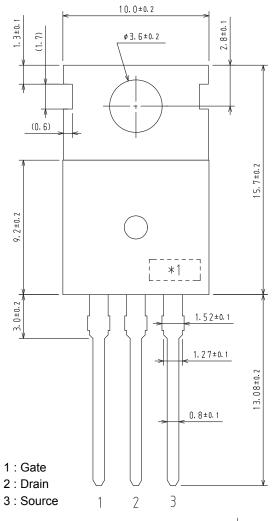


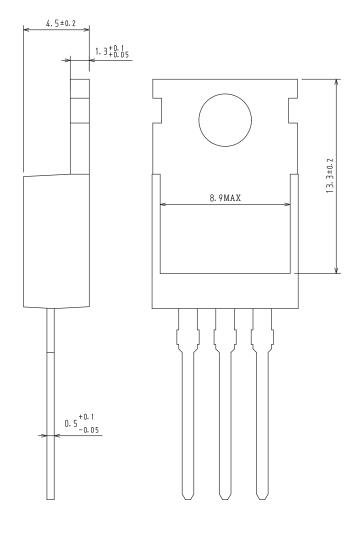
PACKAGE DIMENSIONS

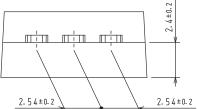
unit: mm

TO-220, 3-Lead / TO-220-3L

CASE 221AU ISSUE O







These dimension do not include mold protrusion

*1 : Lot indication

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
NDPL070N10BG	070N10	TO-220, 3-Lead / TO-220-3L (Pb-Free)	50 / Tube

Note on usage: Since the NDPL070N10B is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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